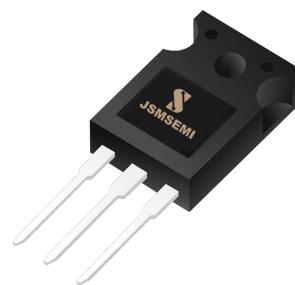


FEATURES

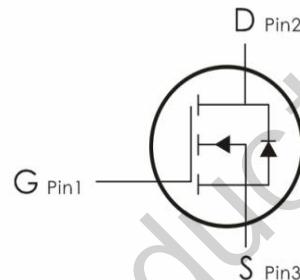
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information		
Device	Package	Marking
IRFP90N20DPBF	TO-247	IRFP90N20D



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
		TO-247	
Drain-Source Voltage ($V_{GS} = 0\text{ V}$)	V_{DSS}	220	V
Continuous Drain Current $V_{GS} = 10\text{ V}$ $T_C = 25^\circ\text{C}$	I_D	95	A
Pulsed Drain Current (note1)	I_{DM}	400	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	1960.2	mJ
Avalanche Current (note1)	I_{AS}	19.8	A
Repetitive Avalanche Energy (note1)	E_{AR}	1176.1	mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	600	W
Peak Diode Recovery dv/dt (note1)	dv/dt	5.0	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	0.89	°C/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	60	

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	220	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 40\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{\text{DS}} = 32\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 125^\circ\text{C}$	--	--	100	
Gate-Source Leakage	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 95\text{A}$ (Note4)	--	25	30	$\text{m}\Omega$
Dynamic						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1.0\text{MHz}$	--	5784	--	pF
Output Capacitance	C_{oss}		--	893	--	
Reverse Transfer Capacitance	C_{rss}		--	561	--	
Total Gate Charge	Q_g	$V_{\text{DD}} = 20\text{V}, I_D = 190\text{A}, V_{\text{GS}} = 10\text{V}$ (Note4)	--	367	--	nC
Gate-Source Charge	Q_{gs}		--	33.8	--	
Gate-Drain Charge	Q_{gd}		--	177	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 20\text{V}, I_D = 190\text{A}, R_G = 10 \Omega, V_{\text{GS}} = 10\text{V}$ (Note4)	--	55	--	ns
Turn-on Rise Time	t_r		--	165	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	1050	--	
Turn-off Fall Time	t_f		--	367	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	90	A
Pulsed Diode Forward Current	I_{SM}		--	--	400	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 95\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{\text{GS}} = 0\text{V}, I_S = 190\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	--	360	--	ns
Reverse Recovery Charge	Q_{rr}		--	5.61	--	μC

Notes

- Repetitive Rating: Pulse width limited by maximum junction temperature
- $L = 10\text{mH}, V_{\text{DD}} = 50\text{V}, R_G = 25 \Omega$, Starting $T_J = 25^\circ\text{C}$
- Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

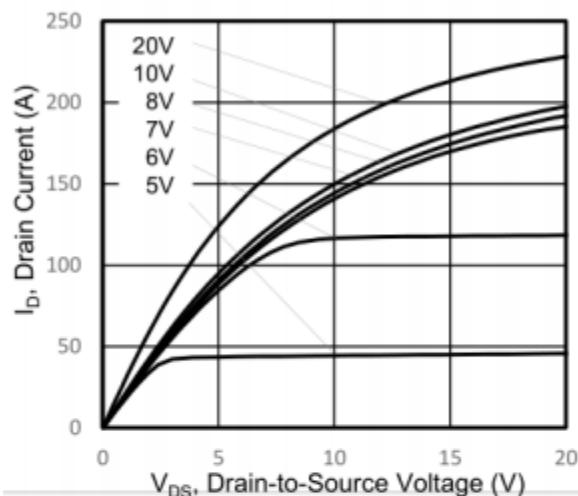


Figure 2. Body Diode Forward Voltage

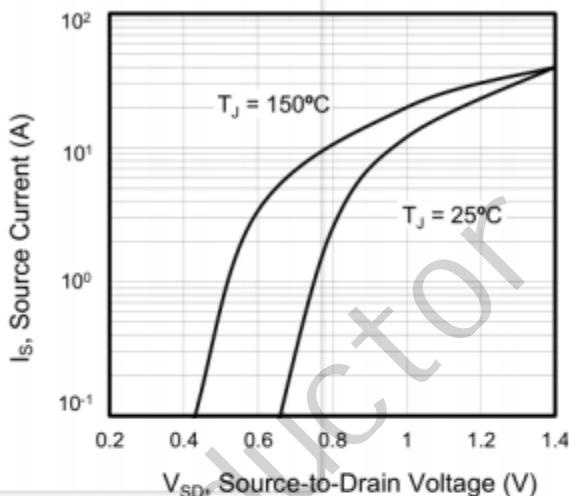


Figure 3. Drain Current vs. Temperature

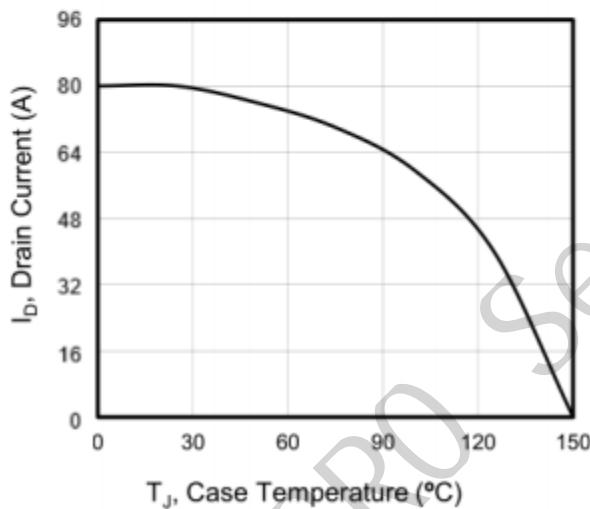


Figure 4. BV_{DSS} Variation vs. Temperature

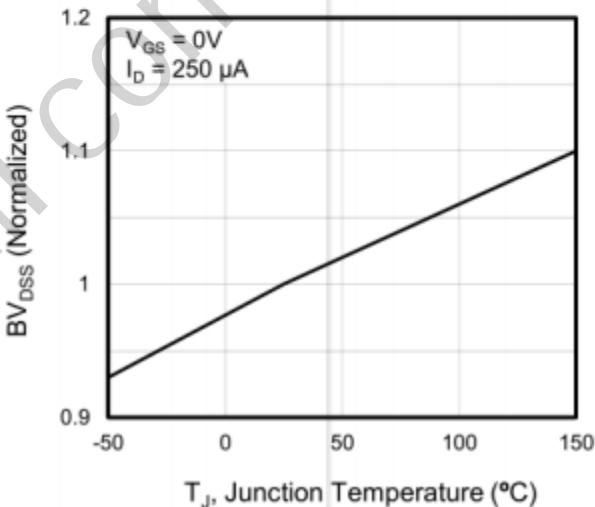


Figure 5. Transfer Characteristics

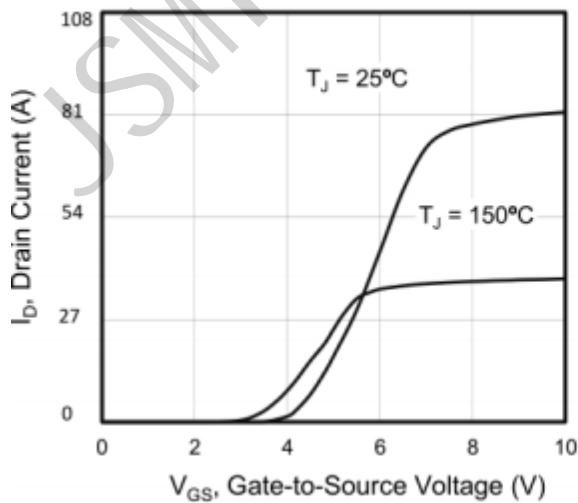
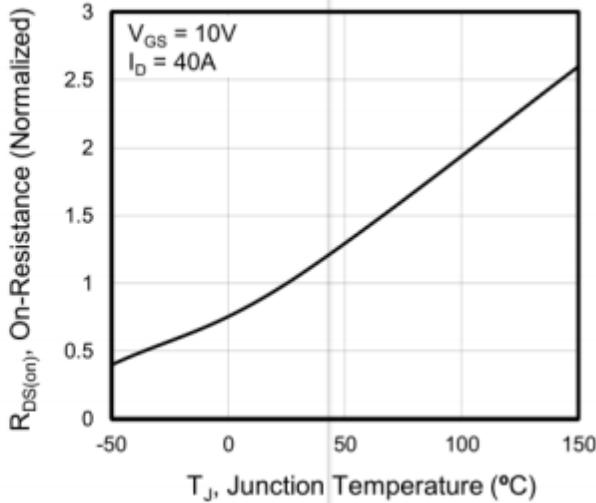


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

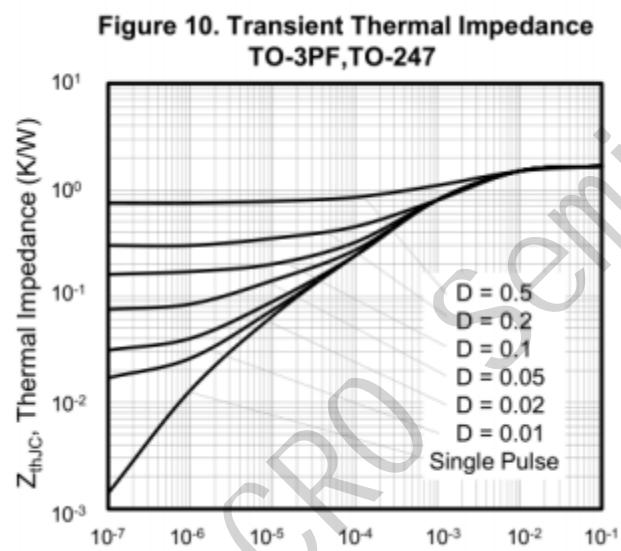
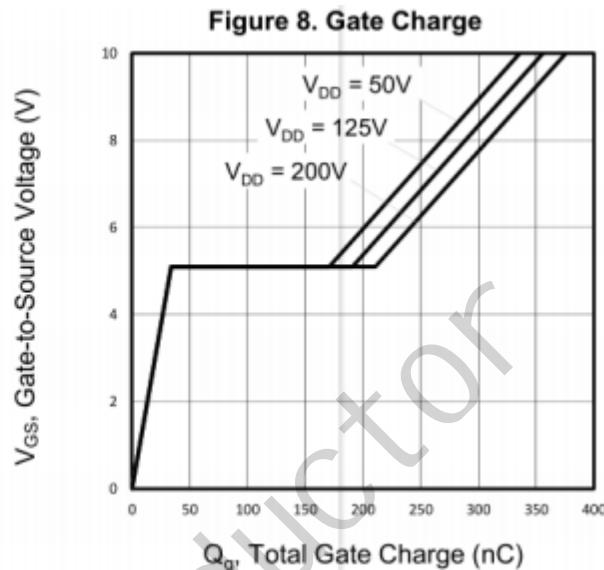
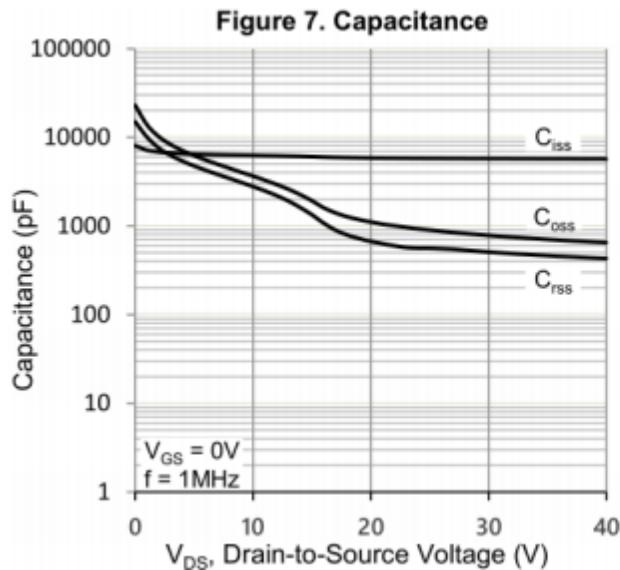


Figure A: Gate Charge Test Circuit and Waveform

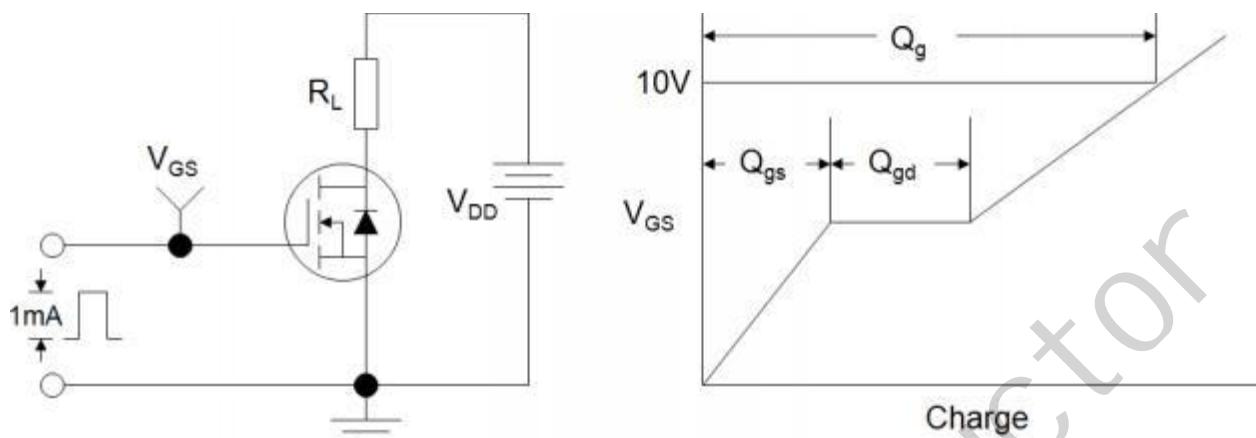


Figure B : Resistive Switching Test Circuit and Waveform

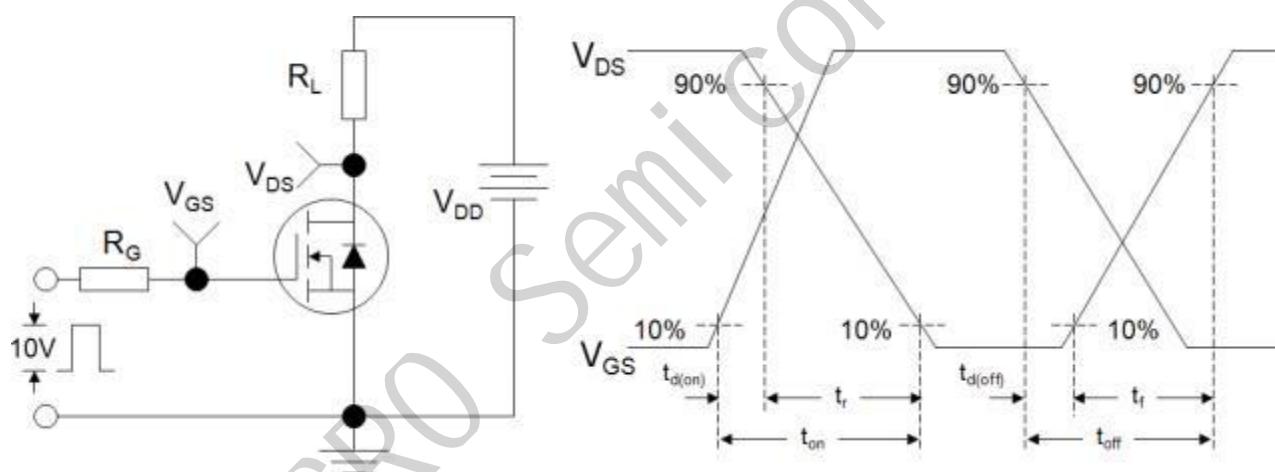
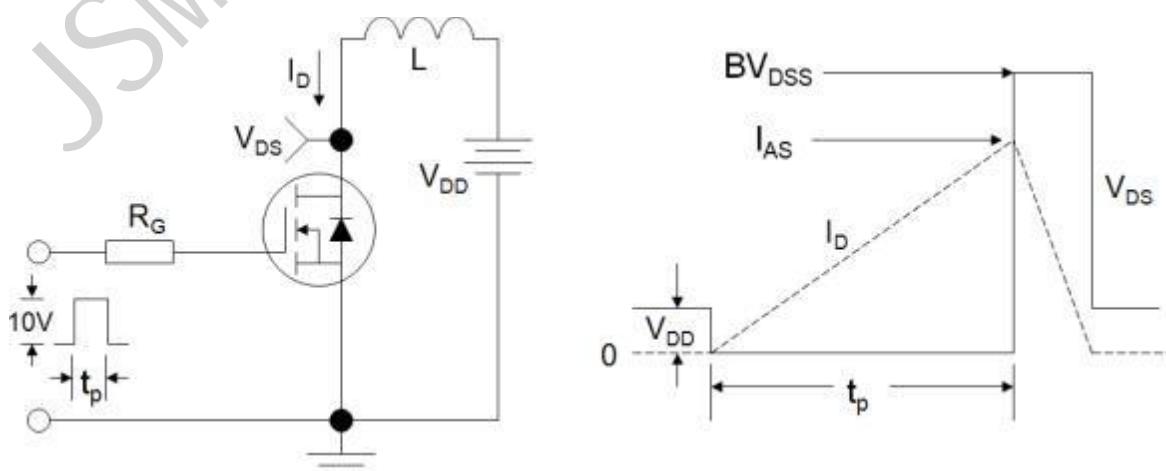
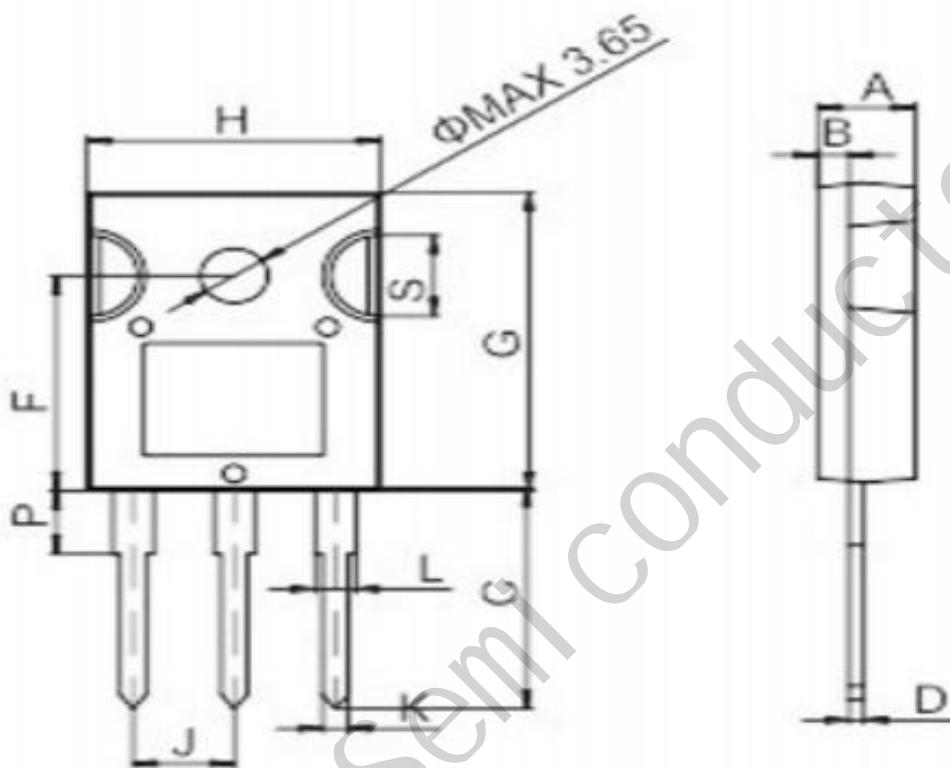


Figure C : Unclamped Inductive Switching Test Circuit and Waveform



TO-247


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.9		5.4	0.193		0.213
B	1.6		2.0	0.063		0.079
C	14.35		15.4	0.565		0.606
D	0.5		0.8	0.020		0.031
F	14.4		15.1	0.567		0.594
G	19.7		20.6	0.775		0.811
H	15.4		16.2	0.606		0.638
J	5.3		5.6	0.209		0.220
K	1.3		1.5	0.051		0.059
L	2.8		3.3	0.110		0.130
P	3.7		4.2	0.146		0.165
S	5.35		5.65	0.211		0.222